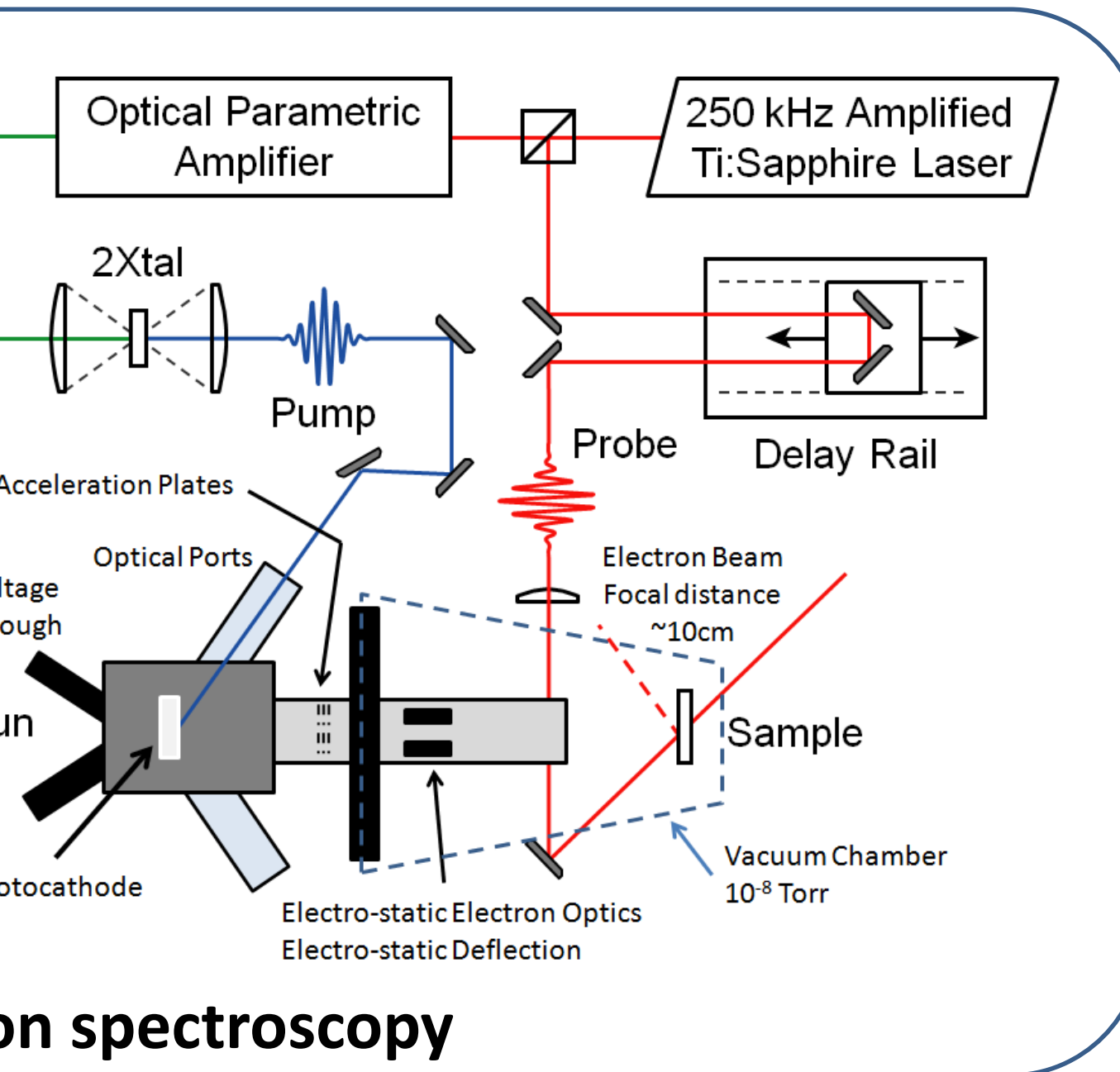
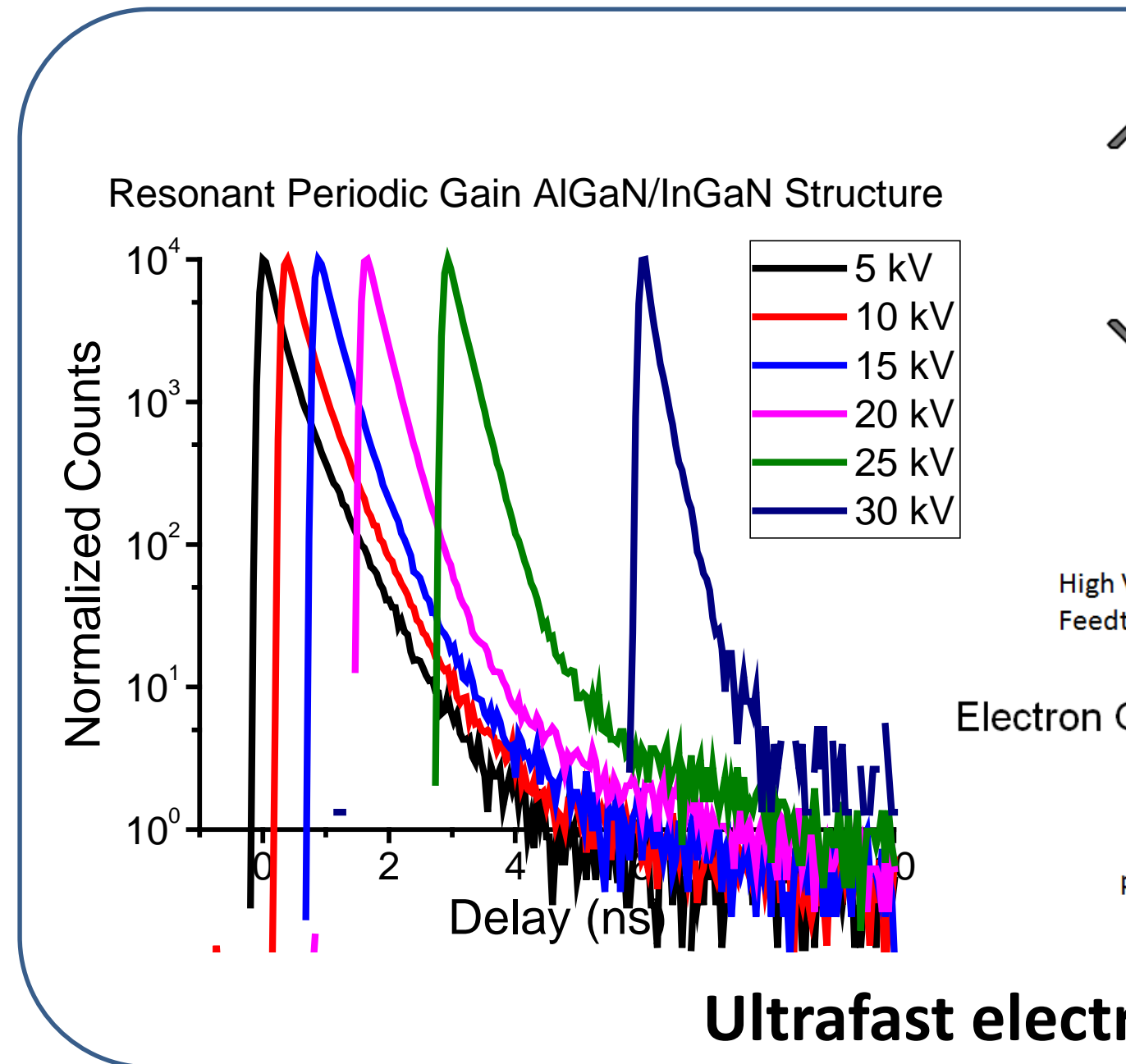
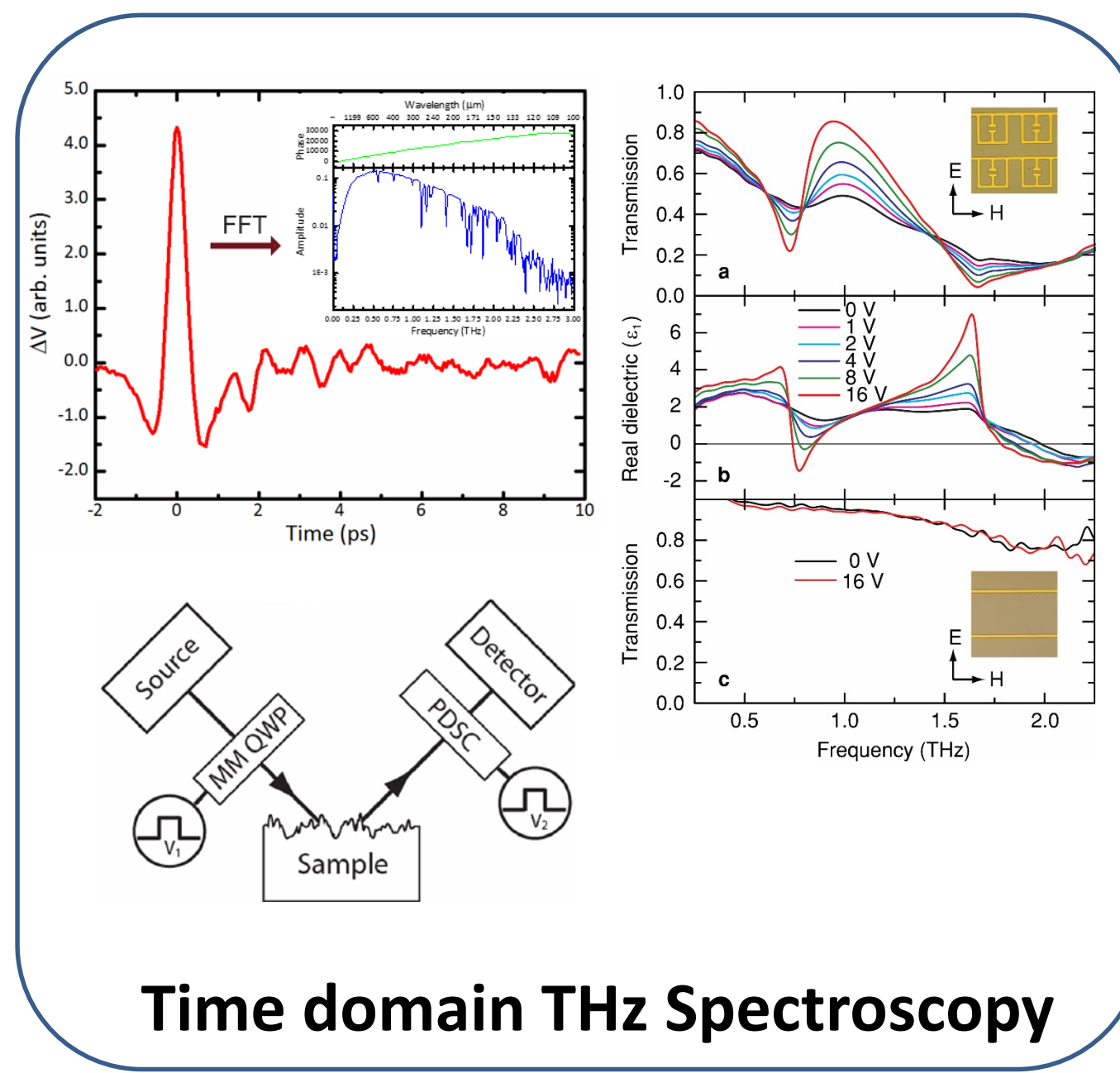
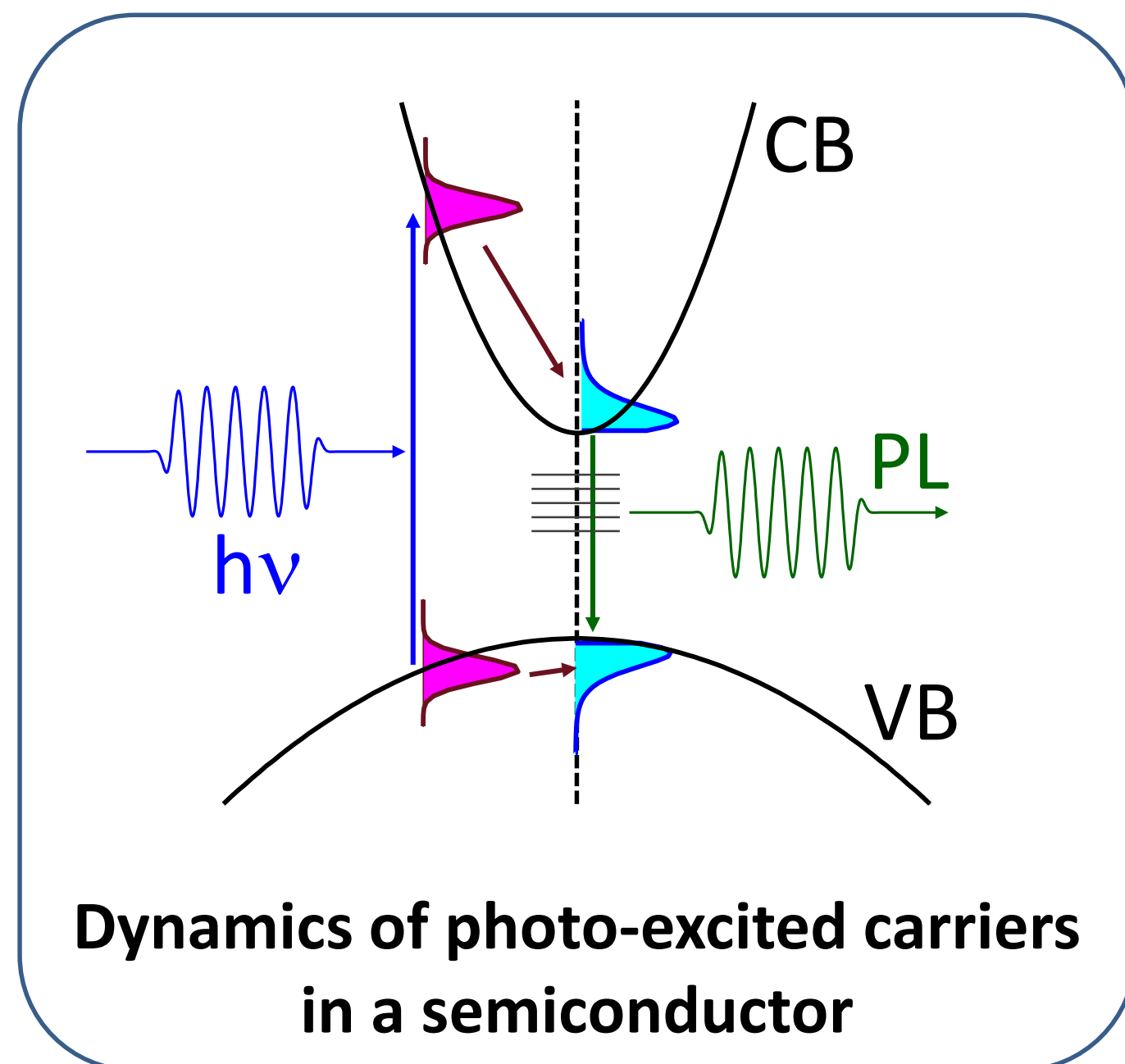


S&T Campaign: Materials Research
Photonics

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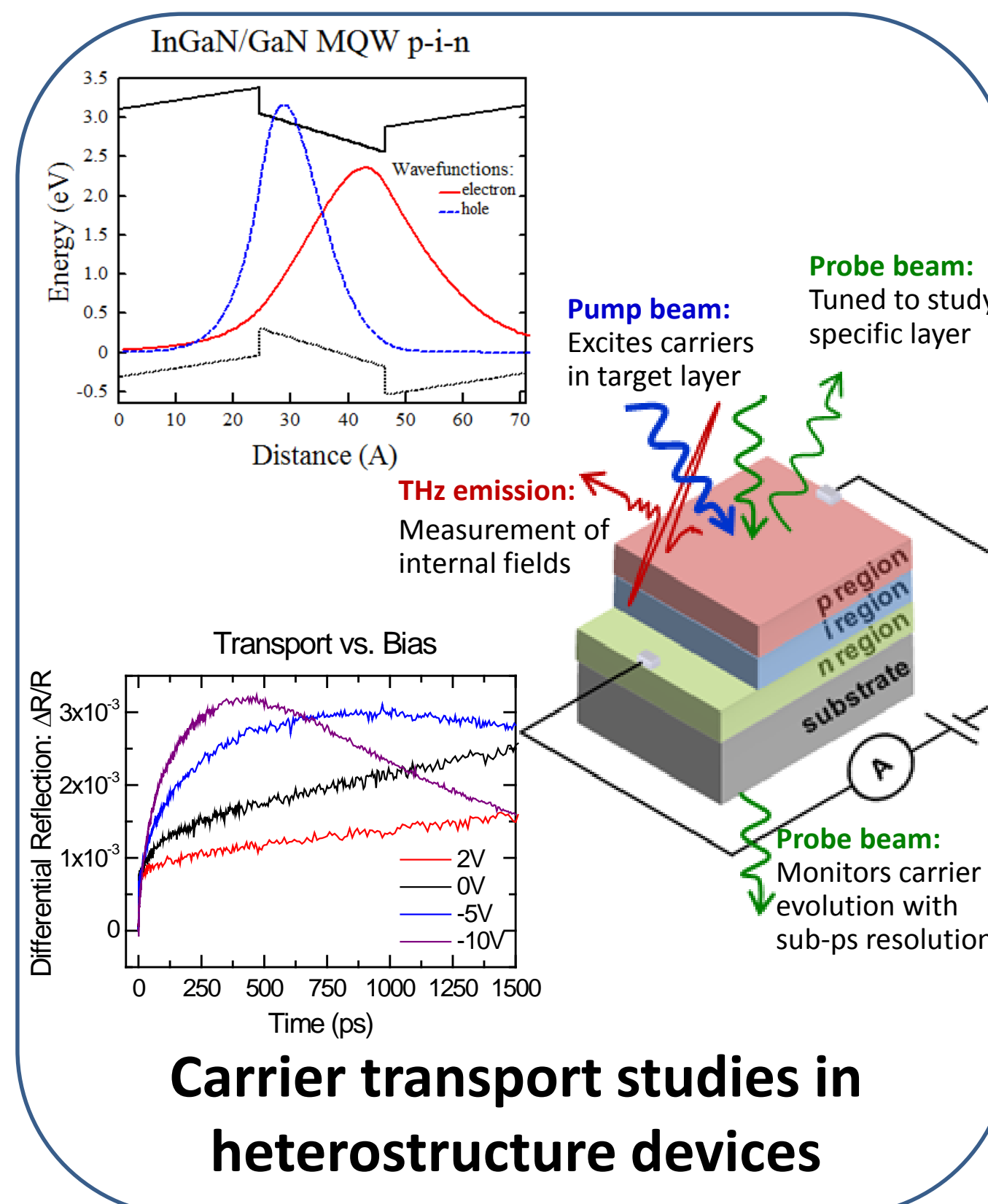
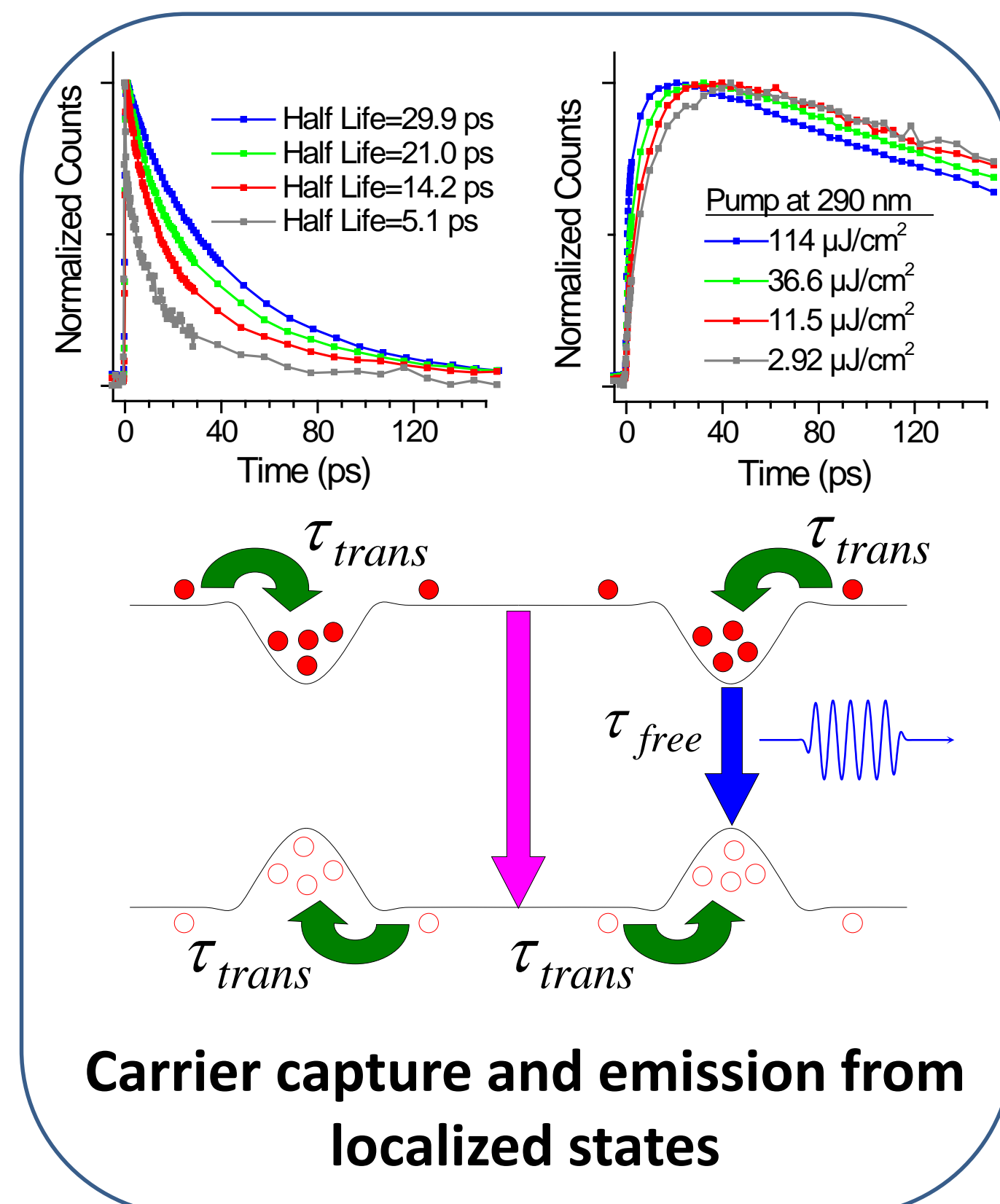
Research Objective

- The study of electron, phonon, and other quasi-particle dynamics in emergent materials and state-of-the-art devices
- Investigate quantum phenomenon in semiconductor-light interactions using coherence spectroscopy for applications in quantum information



Challenges

- Identifying a combination of sample design and diagnostic techniques to extract information on relevant carrier dynamics/phenomena
- Developing robust models to connect observations with material/device properties of interest
- Working in the ultraviolet and far-infrared spectrums



ARL Facilities and Capabilities Available to Support Collaborative Research

- Three 250-kHz Coherent RegA Ti:Sapphire lasers
 - 100-fs optical pulses at 800 nm with > 6 μJ/pulse
 - Optical parametric amplifiers (OPA) tunable through the visible and down to 2.4 μm
 - Doubled OPA gives pulses tunable through the UV
 - Difference frequency generator (DFG) pulses (2 – 10 μm)
- One 76-MHz Spectra-Physics Inspire OPA
- Broad range of time-resolved detection techniques
 - Time-correlated single photon counting with a multi-channel plate PMT; 25-ps resolution
 - Ultrafast streak camera with synchronous sweep (3-ps resolution) or triggered sweep drivers
 - Optical gating by frequency mixing in a non-linear crystal; sub-picosecond time resolution
 - Various optical delay rails and modulators for differential transmission and reflection, pump-probe, and four wave mixing techniques
- Optical THz pulse generation and detection for time-domain THz spectroscopy
- Developing novel Ultrafast Electron Spectroscopy (UES) system with picosecond electron pulse excitations
- Research Highlights:
 - Investigation of Trap States in Mid-Wavelength Infrared Type II Superlattices using Time-Resolved Photoluminescence
 - Blair C. Connelly et al, J. Electron. Mat. 42, 3203, 2014.
 - Time-Resolved Electroabsorption Measurement of Carrier Velocity in Inverted Polarity In_{1-x}Ga_xN/GaN Heterostructures due to Internal Electric Fields
 - Blair C. Connelly et al, Phys. Status Solidi C 11, 682, 2013
 - Theoretical and Experimental Study of Dynamics of Photoexcited Carriers in GaN
 - Gregory A. Garrett et al, J. Appl. Phys. 114, 233106, 2013.
 - Terahertz Studies of Carrier Localization in Spontaneously Forming Polar Lateral Heterostructures
 - Grace D. Metcalfe et al, Phys. Status Solidi RRL 7, 993, 2013.
 - Pseudomorphically Grown Ultraviolet C Photopumped Lasers on Bulk AlN Substrates
 - Gregory A. Garrett et al, Appl. Phys. Exp., 4, 092101, 2011.
 - Crystal-Field Split Levels of Nd³⁺ Ions in GaN Measured by Luminescence Spectroscopy
 - Grace D. Metcalfe et al, J. Appl. Phys., 105, 053101, 2009.
 - Unique ARL expertise in Ultraviolet, Mid- and Long-Wavelength IR, and time-resolved THz spectroscopy

Complementary Expertise / Facilities / Capabilities Sought in Collaboration

- Modeling of ultrafast carrier dynamics/phenomena
- Innovative materials and device designs
 - UV optoelectronics (laser diodes, LEDs, detectors)
 - Mid- and long-wavelength IR detectors
 - Coherence effects in wide bandgap semiconductors
 - Metamaterials and plasmonics
 - Van der Waals heterostructures and topological insulators